Erratum

Blocking of Silicon Oxidation by Low-Dose Nitrogen Implantation

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The second Taly-step measurement value in Table 1 on p. 74 (samples 12–0, 12–2) was 94 ± 4 nm instead of 46 ± 4 nm. Furthermore, the sentence “However, it was found that the doping can be minimized by shallow implantation combined with prolonged annealing” in Sect. 2.4 on p. 76 was not confirmed by any measurements.